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Center Drive West, Suite 1050, Los Angeles, CA 90045 (US).

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(71) Applicant (for all designated States except US): THE REGENTS OF THE UNIVERSITY OF CALIFORNIA [US/US]; 1111 Franklin Street, 12th Floor, Oakland, CA 94607 (US).

(72) Inventors; and

(75) Inventors/Applicants (for US only): HASKELL, Benjamin, A. [US/US]; 724 Kroeber Walk, #207, Goleta, CA 93117 (US). CRAVEN, Michael, D. [US/US]; 68 1/2 Deerhurst Drive, Goleta, CA 93117 (US). FINI, Paul, T. [US/US]; 218 West Mason Street, Santa Barbara, CA 93101 (US). DENBAARS, Steven, P. [US/US]; 287 King Daniel Lane, Goleta, CA 93117 (US). SPECK, James, S. [US/US]; 947 West Campus Lane, Goleta, CA 93117 (US). NAKAMURA, Shuji [JP/US]; 4517 Vieja Drive, Santa Barbara, CA 93110 (US).

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(54) Title: GROWTH OF REDUCED DISLOCATION DENSITY NON-POLAR GALLIUM NITRIDE BY HYDRIDE VAPOR PHASE EPITAXY

(57) Abstract: Lateral epitaxial overgrowth (LEO) of non-polar a-plane gallium nitride (GaN) films by hydride vapor phase epitaxy (HVPE) results in significantly reduced defect density.